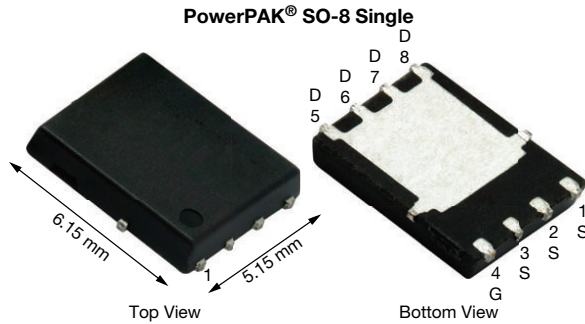


N-Channel 150 V (D-S) MOSFET



FEATURES

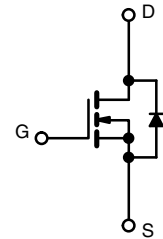
- TrenchFET® Gen V power MOSFET
- Very low $R_{DS} \times Q_g$ figure-of-merit (FOM)
- Tuned for the lowest $R_{DS} \times Q_{OSS}$ FOM
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Synchronous rectification
- Primary side switch
- DC/DC converters
- Power supplies
- Motor drive control



N-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	150
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.0079
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5$ V	0.0085
Q_g typ. (nC)	35.1
I_D (A)	77.4
Configuration	Single

ORDERING INFORMATION	
Package	PowerPAK SO-8
Lead (Pb)-free and halogen-free	SiR570DP-T1-RE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	150	V	
Gate-source voltage	V_{GS}	± 20		
Continuous drain current ($T_J = 150$ °C)	$T_C = 25$ °C	77.4	A	
	$T_C = 70$ °C	61.9		
	$T_A = 25$ °C	19 ^{b, c}		
	$T_A = 70$ °C	15.2 ^{b, c}		
Pulsed drain current ($t = 100$ μ s)	I_{DM}	200	A	
Continuous source-drain diode current	$T_C = 25$ °C	94		
	$T_A = 25$ °C	5.6 ^{b, c}		
Single pulse avalanche current	$L = 0.1$ mH	I_{AS}	30	mJ
Single pulse avalanche energy		E_{AS}	45	
Maximum power dissipation	$T_C = 25$ °C	P_D	104	W
	$T_C = 70$ °C		66.6	
	$T_A = 25$ °C		6.25 ^{b, c}	
	$T_A = 70$ °C		4 ^{b, c}	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature) ^c		260		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient ^b	$t \leq 10$ s	R_{thJA}	15	20	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	0.9	1.2	

Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 10$ s
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 54 °C/W
- $T_C = 25$ °C



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 1 mA	150	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	I _D = 10 mA	-	125	-	mV/°C
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J	I _D = 250 μA	-	-6.9	-	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2	-	4	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 120 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 120 V, V _{GS} = 0 V, T _J = 70 °C	-	-	15	
On-state drain current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	40	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A	-	0.0065	0.0079	Ω
		V _{GS} = 7.5 V, I _D = 15 A	-	0.0070	0.0085	
Forward transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 20 A	-	80	-	S
Dynamic ^b						
Input capacitance	C _{ISS}	V _{DS} = 75 V, V _{GS} = 0 V, f = 1 MHz	-	3740	-	pF
Output capacitance	C _{OSS}		-	330	-	
Reverse transfer capacitance	C _{RSS}		-	6.5	-	
Total gate charge	Q _g	V _{DS} = 75 V, V _{GS} = 10 V, I _D = 20 A	-	46.9	71	nC
		V _{DS} = 75 V, V _{GS} = 7.5 V, I _D = 20 A	-	35.1	53	
Gate-source charge	Q _{gs}		-	18.1	-	
Gate-drain charge	Q _{gd}		-	4.2	-	
Output charge	Q _{OSS}	V _{DS} = 75 V, V _{GS} = 0 V	-	111	-	
Gate resistance	R _g	f = 1 MHz	0.4	1.1	1.8	Ω
Turn-on delay time	t _{d(on)}	V _{DD} = 75 V, R _L = 3.75 Ω, I _D ≅ 20 A, V _{GEN} = 10 V, R _g = 1 Ω	-	17	34	ns
Rise time	t _r		-	16	32	
Turn-off delay time	t _{d(off)}		-	29	58	
Fall time	t _f		-	21	42	
Turn-on delay time	t _{d(on)}	V _{DD} = 50 V, R _L = 3.75 Ω, I _D ≅ 20 A, V _{GEN} = 7.5 V, R _g = 1 Ω	-	21	42	
Rise time	t _r		-	74	148	
Turn-off delay time	t _{d(off)}		-	27	54	
Fall time	t _f		-	22	44	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	94	A
Pulse diode forward current	I _{SM}		-	-	200	
Body diode voltage	V _{SD}	I _S = 5 A, V _{GS} = 0 V	-	0.75	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs, T _J = 25 °C	-	84	168	ns
Body diode reverse recovery charge	Q _{rr}		-	221	442	nC
Reverse recovery fall time	t _a		-	65	-	ns
Reverse recovery rise time	t _b		-	19	-	

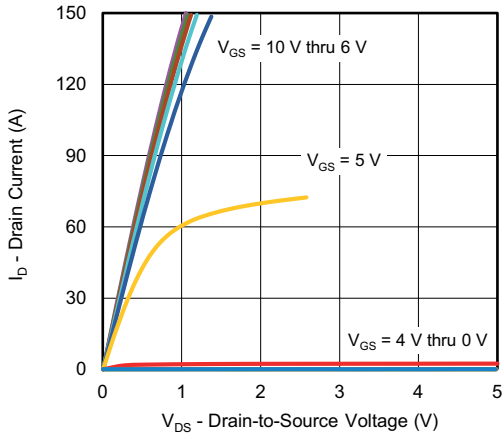
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b. Guaranteed by design, not subject to production testing

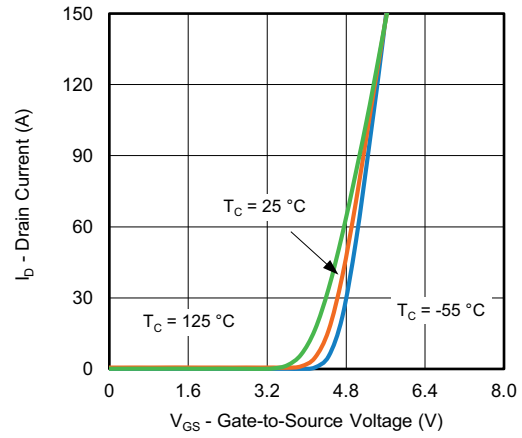
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



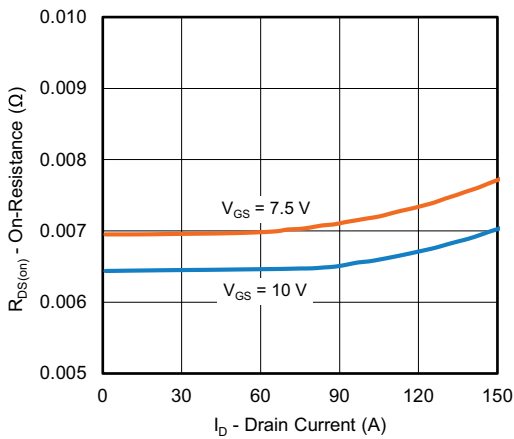
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



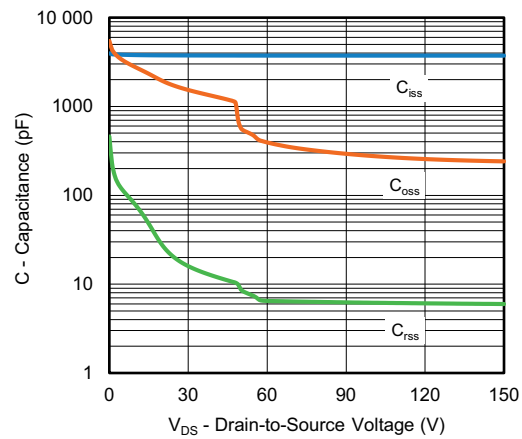
Output Characteristics



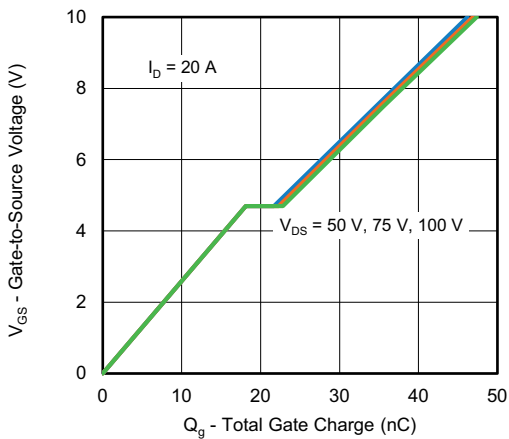
Transfer Characteristics



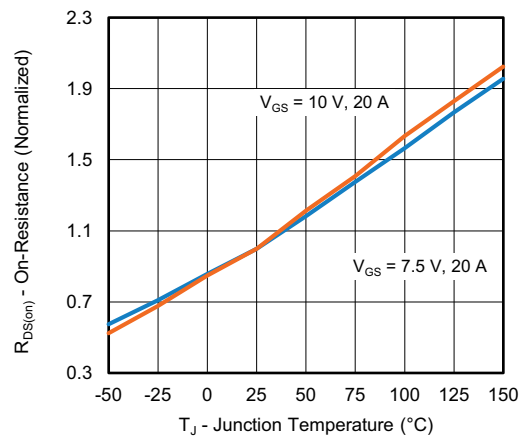
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

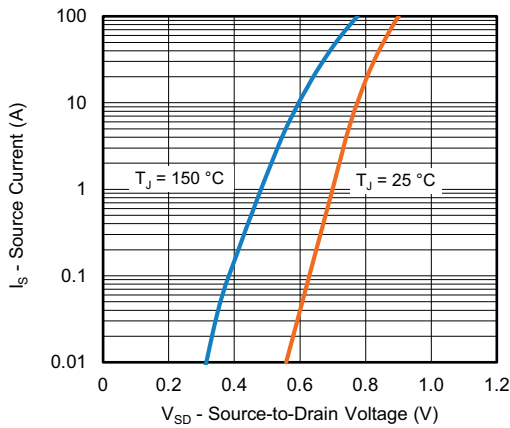


Gate Charge

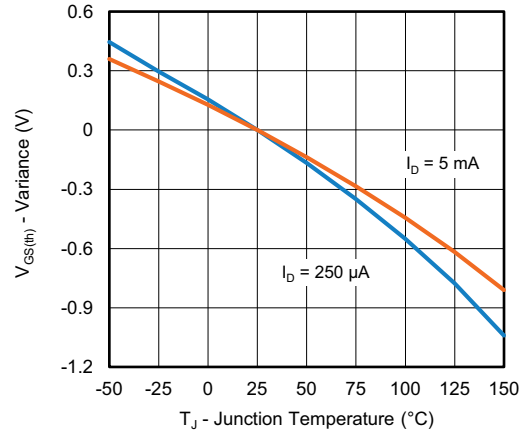


On-Resistance vs. Junction Temperature

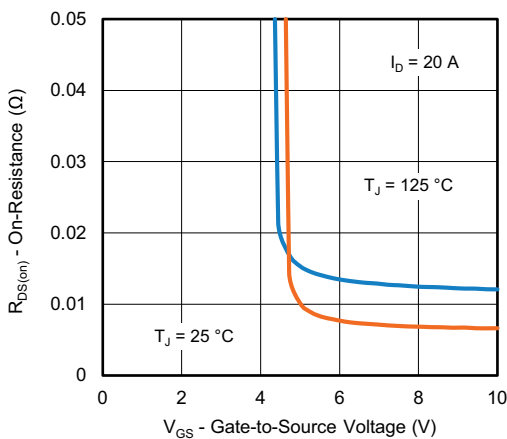
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



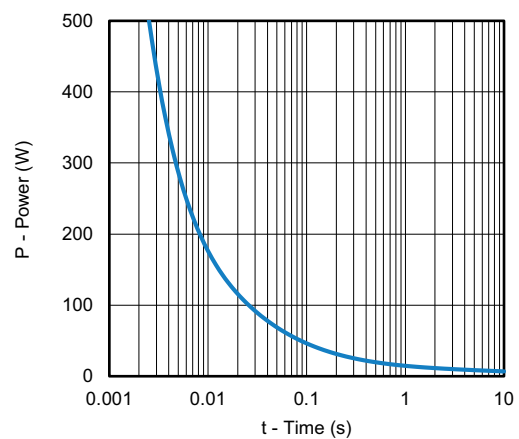
Source-Drain Diode Forward Voltage



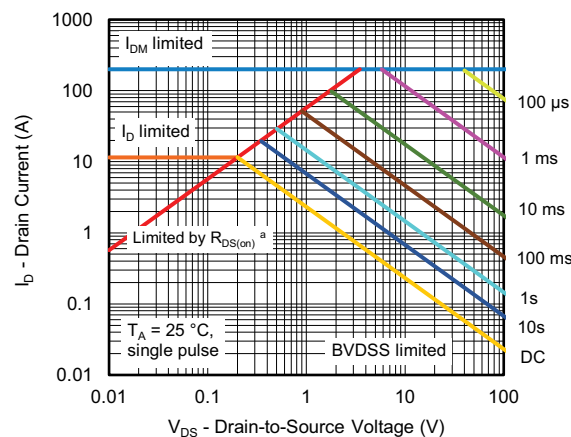
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



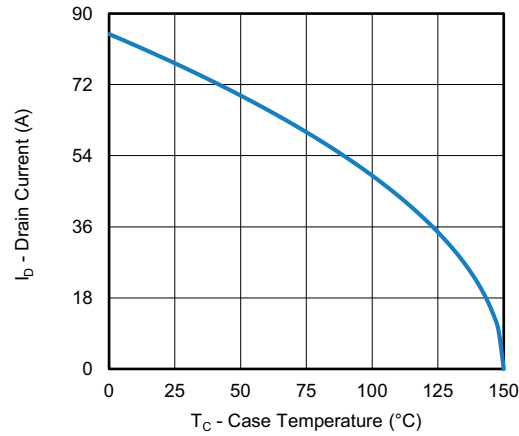
Safe Operating Area, Junction-to-Ambient

Note

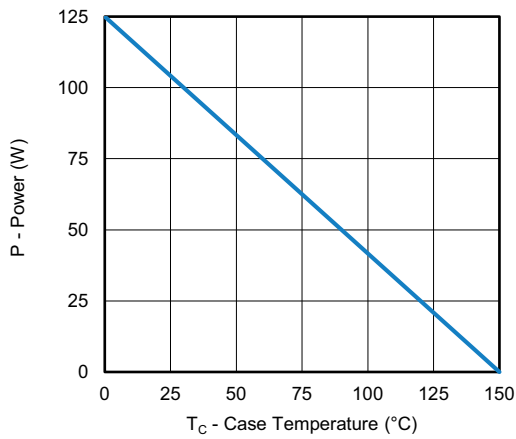
a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



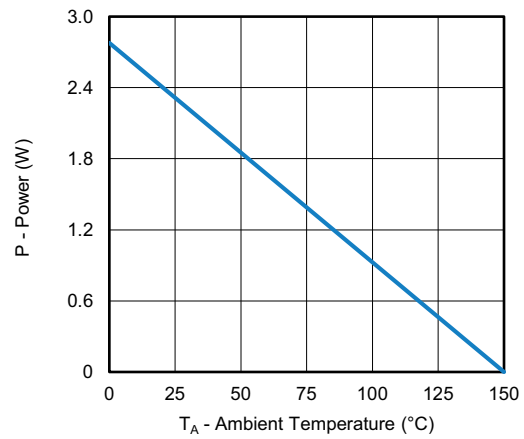
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating ^a



Power, Junction-to-Case



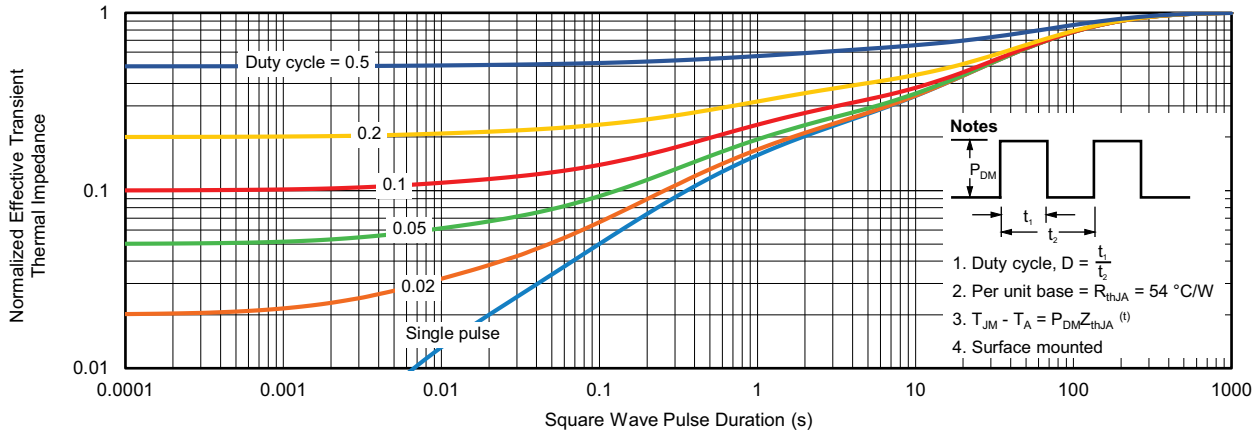
Power, Junction-to-Ambient

Note

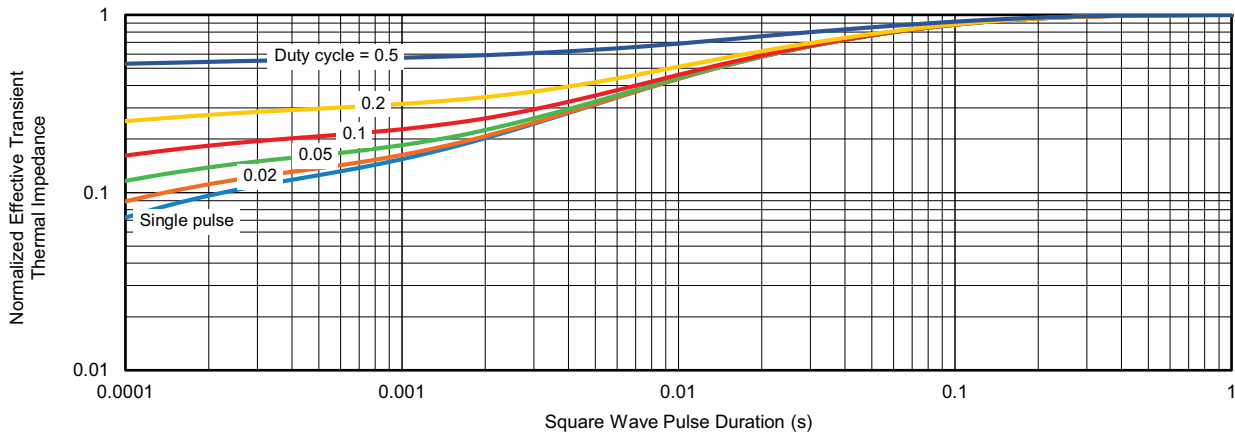
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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